

**Notice of References Cited**Application/Control No  
10/055,157Applicant(s)/Patent Under  
Reexamination  
LIN ET AL.Examiner  
Anh D. MaiArt Unit  
2814

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-4836885	06-1989	Breiten et al.	438/435
	B	US-5872058	02-1999	Van Cleemput et al.	438/692
	C	US-6048771	04-2000	Lin et al.	438/424
	D	US-6069056	03-2000	Son et al.	438/424
	E	US-6071792	06-2000	Kim et al.	438/424
	F	US-6146975	11-2000	Kuehne et al.	438/435
	G	US-6159822	12-2000	Yang et al.	438/427
	H	US-6228741	05-2002	Walsh et al.	438/424
	I	US-6313010	11-2001	Nag et al.	438/435
	J	US-5494854	02-1996	Jain	438/692
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP-2000-306992	11-2000	Japan	Kishimoto	H01L 21/76
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	G.Y. Lee et al. A Low Redeposition Rate High Density Plasma CVD Process for High Aspect Ratio 175 nm Technology and Beyond. IEEE 1999, pp. 152-154.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.